TOSHIBA Transistor Silicon NPN Epitaxial Planar Type

# 2SC5089

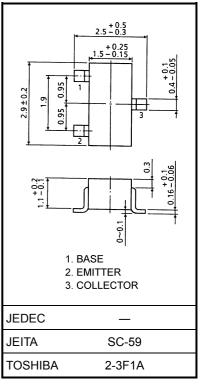
### VHF~UHF Band Low Noise Amplifier Applications

Unit: mm

- Low noise figure, high gain.
- NF = 1.1dB,  $|S_{21e}|^2 = 13dB$  (f = 1 GHz)

### Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit	
Collector-base voltage	V <sub>CBO</sub>	20	V	
Collector-emitter voltage	V <sub>CEO</sub>	10	V	
Emitter-base voltage	V <sub>EBO</sub>	1.5	V	
Base current	Ι <sub>Β</sub>	20	mA	
Collector current	I <sub>C</sub>	40	mA	
Collector power dissipation	P <sub>C</sub>	150	mW	
Junction temperature	Tj	125	°C	
Storage temperature range	T <sub>stg</sub>	-55~125	°C	



#### Weight: 0.012 g (typ.)

# **Microwave Characteristics (Ta = 25°C)**

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit	
Transition frequency	f <sub>T</sub>	$V_{CE} = 8 \text{ V}, I_{C} = 20 \text{ mA}$	7	10	_	GHz	
Insertion gain	S <sub>21e</sub>   <sup>2</sup> (1)	$V_{CE} = 8 \text{ V}, I_{C} = 20 \text{ mA}, f = 1 \text{ GHz}$ 10		13	_	dB	
	S <sub>21e</sub>   <sup>2</sup> (2)	V <sub>CE</sub> = 8 V, I <sub>C</sub> = 20 mA, f = 2 GHz				ub	
Noise figure	NF (1)	$V_{CE} = 8 \text{ V}, I_{C} = 5 \text{ mA}, f = 1 \text{ GHz}$	_	1.1	2.5	dB	
Noise ligure	NF (2)	$V_{CE} = 8 \text{ V}, I_{C} = 5 \text{ mA}, f = 2 \text{ GHz}$	_	1.7		U.B	

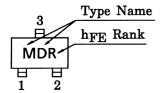
# **Electrical Characteristics (Ta = 25°C)**

Characteristics	Characteristics Symbol		Min	Тур.	Max	Unit
Collector cut-off current	I <sub>CBO</sub>	$V_{CB} = 10 \text{ V}, I_{E} = 0$	_	_	1	μΑ
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> = 1 V, I <sub>C</sub> = 0	_	_	1	μА
DC current gain	h <sub>FE</sub> (Note 1)	V <sub>CE</sub> = 8 V, I <sub>C</sub> = 20 mA	50	_	160	
Output capacitance	C <sub>ob</sub>	V <sub>CB</sub> = 10 V, I <sub>E</sub> = 0, f = 1 MHz (Note 2)	_	0.7	_	pF
Reverse transfer capacitance	C <sub>re</sub>	VCB = 10  V, 1E = 0, 1 = 1  WITZ  (Note 2)	_	0.5	0.95	pF

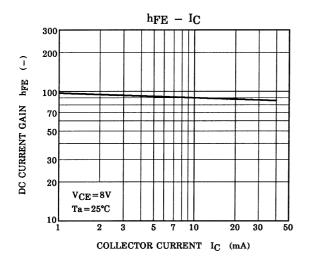
Note 1: hFE classification R: 50~100, O: 80~160

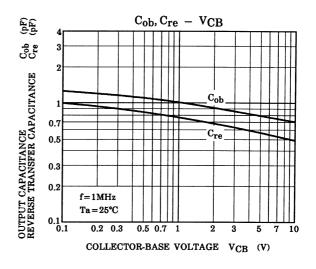
Note 2:  $C_{\text{re}}$  is measured by 3 terminal method with capacitance bridge.

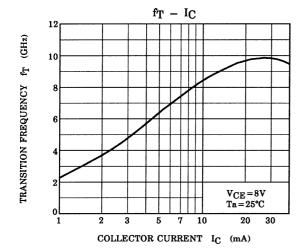
# Marking

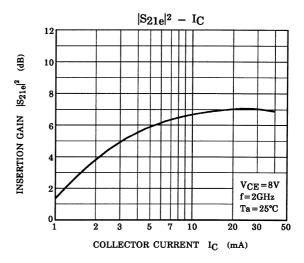


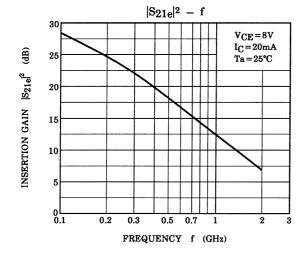
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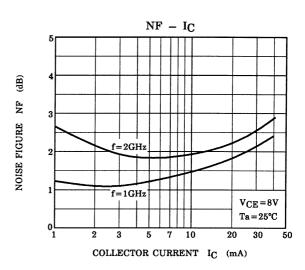




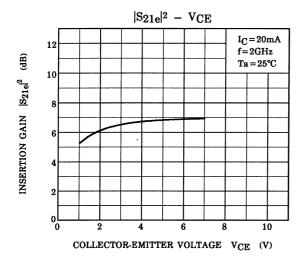


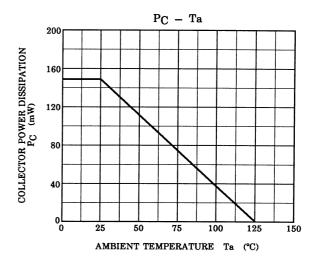






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# S-Parameter $Z_O = 50 \Omega$ , Ta = 25°C

# $V_{CE} = 8 V$ , $I_C = 5 mA$

Frequency	S	11	S2	21	S1	12	S2	22
(MHz)	Mag.	Ang.	Mag.	Ang.	Mag.	Ang.	Mag.	Ang.
200	0.653	-48.5	10.080	136.2	0.046	63.5	0.766	-27.9
400	0.420	-82.1	7.242	112.7	0.069	57.6	0.561	-35.0
600	0.284	-105.7	5.393	98.9	0.086	57.9	0.466	-35.4
800	0.214	-126.0	4.245	89.7	0.103	59.4	0.420	-34.9
1000	0.169	-146.7	3.508	82.2	0.121	60.6	0.394	-34.7
1200	0.155	-166.4	3.012	75.9	0.140	61.9	0.382	-35.1
1400	0.152	174.1	2.645	70.2	0.162	62.1	0.374	-36.1
1600	0.154	156.7	2.350	65.0	0.182	61.3	0.363	-38.5
1800	0.161	145.9	2.136	60.2	0.202	60.5	0.355	-41.0
2000	0.181	134.5	1.972	55.8	0.224	60.6	0.345	-44.0

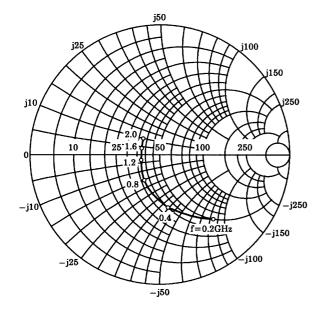
# $V_{CE} = 8 V$ , $I_C = 20 mA$

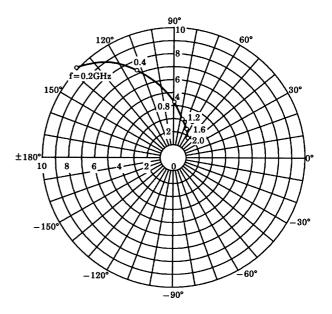
Frequency	y S11		S21		S12		S22	
(MHz)	Mag.	Ang.	Mag.	Ang.	Mag.	Ang.	Mag.	Ang.
200	0.275	-80.2	17.464	114.7	0.033	68.9	0.506	-36.6
400	0.147	-116.5	9.693	97.8	0.057	72.0	0.353	-32.4
600	0.097	-150.0	6.680	88.8	0.082	72.7	0.313	-27.9
800	0.083	179.5	5.088	82.3	0.106	72.1	0.300	-25.9
1000	0.084	151.3	4.141	76.7	0.131	71.2	0.295	-25.2
1200	0.095	135.6	3.497	72.2	0.156	69.8	0.295	-25.7
1400	0.108	124.2	3.058	67.7	0.182	67.7	0.297	-27.3
1600	0.121	113.8	2.699	63.2	0.206	65.2	0.289	-30.1
1800	0.128	108.4	2.432	59.2	0.228	63.0	0.283	-33.2
2000	0.146	104.2	2.241	55.5	0.253	61.6	0.274	-36.5

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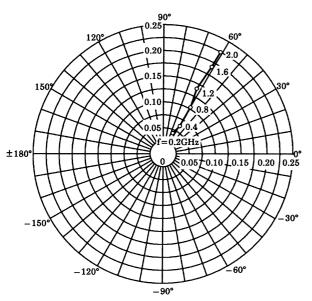
 $\begin{array}{l} S_{11e} \\ V_{CE} = 8V \\ I_{C} = 5mA \\ Ta = 25^{\circ}C \\ (UNIT:\Omega) \end{array}$ 

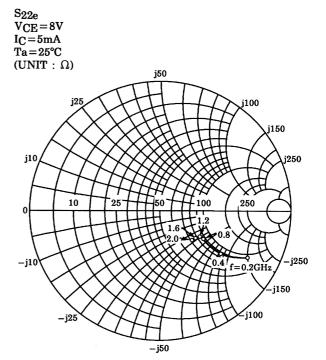






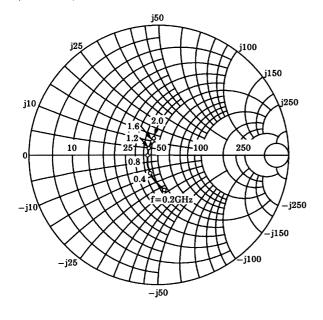
 $S_{12e}$   $V_{CE} = 8V$   $I_{C} = 5mA$  $T_{a} = 25^{\circ}C$ 

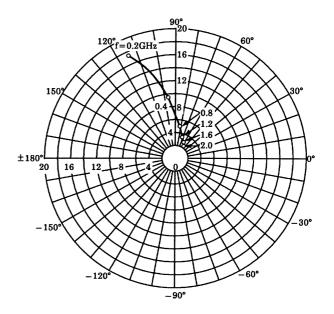




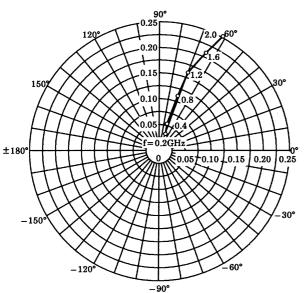
 $\begin{array}{l} S_{11e} \\ V_{CE} = 8V \\ I_{C} = 20 mA \\ Ta = 25 ^{\circ}C \\ (UNIT:\Omega) \end{array}$ 

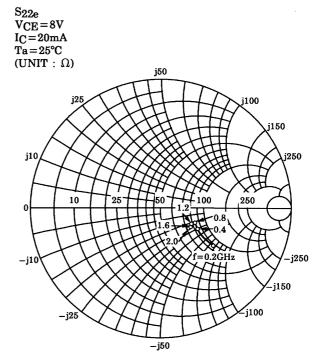






 $\begin{array}{l} S_{12e} \\ V_{CE} = 8V \\ I_{C} = 20 mA \\ Ta = 25 ^{\circ}C \end{array}$ 





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